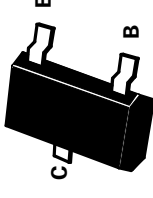


**SOT23 PNP SILICON PLANAR
SWITCHING TRANSISTORS**

ISSUE 2 – SEPTEMBER 95

**BSS82B
BSS82C**

PARTMARKING DETAILS - BSS82B - CL
BSS82C - CM



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-800	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{TOT}	330	mW
Operating and Storage Temperature Range	t_j, t_{stg}	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-60		V	$I_C = -10\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-60		V	$I_C = -10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			$I_E = -10\mu A$
Collector Cut-Off Current	I_{CBO}		-10 -10	nA μA	$V_{CB} = -50V, V_{EB} = -50V, T_{amb} = 150^{\circ}C$
Emitter Cut-Off Current	I_{EBO}		-10	nA	$V_{BE} = -3V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.4 -1.6	V	$I_C = -150mA, I_B = -15mA^*$ $I_C = -500mA, I_B = 50mA^*$
Static Forward Current Transfer Ratio	h_{FE}	40 100	300		$I_C = 150mA, V_{CE} = 10V$ $I_C = 150mA, V_{CE} = 10V$
Transition Frequency	f_T	200		MHz	$V_{CE} = 20V, I_C = -50mA, f = 100MHz$
Output Capacitance	C_{obo}		8	pF	$V_{CB} = -10V, f = 1MHz$
Delay Time	t_d		10	ns	
Rise Time	t_r		40	ns	
Storage Time	t_s		80	ns	$V_{CC} = -30V, I_C = -150mA$ $I_{B1} = -I_{B2} = -15mA$
Fall Time	t_f		30	ns	

* Measured under pulsed conditions. Pulse width = 300 μs . Duty cycle 2%